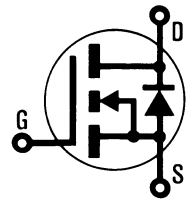
INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS

N-CHANNEL POWER MOSFETs



IRFJ220 IRFJ221 IRFJ222 IRFJ223

200 Volt, 0.8 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

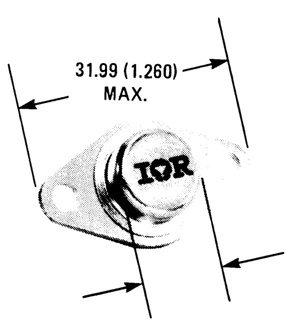
Features:

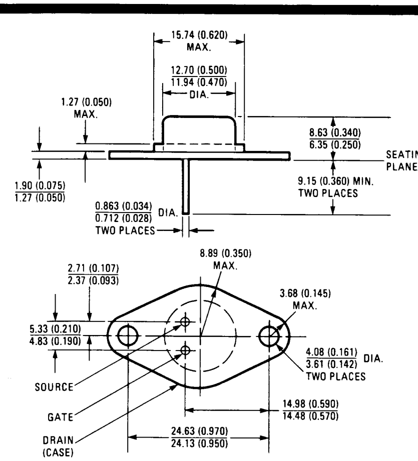
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ220	200V	0.8Ω	5.0A
IRFJ221	150V	0.8Ω	5.0A
IRFJ222	200V	1.2Ω	4.0A
IRFJ223	150V	1.2Ω	4.0A

CASE STYLE AND DIMENSIONS





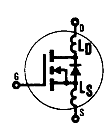
Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

IRFJ220, IRFJ221, IRFJ222, IRFJ223 Devices

Absolute Maximum Ratings

	Parameter	IRFJ220	IRFJ221	IRFJ222	IRFJ223	Units
V_{DS}	Drain - Source Voltage ①	200	150	200	150	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	200	150	200	150	V
I_D @ T_C = 25°C	Continuous Drain Current	5.0	5.0	4.0	4.0	A
I_D @ T_C = 100°C	Continuous Drain Current	3.0	3.0	2.5	2.5	A
I_{DM}	Pulsed Drain Current ③	20	20	16	16	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	40 (See Fig. 14)				W
	Linear Derating Factor	0.32 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 20	20	16	16	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	−55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

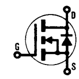
Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain - Source Breakdown Voltage	IRFJ220 IRFJ222	200	—	—	V	V_{GS} = 0V
	IRFJ221 IRFJ223	150	—	—	V	I_D = 250μA
$V_{GS(th)}$ Gate Threshold Voltage	ALL	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS} Gate - Source Leakage Forward	ALL	—	—	100	nA	V_{GS} = 20V
I_{GSS} Gate - Source Leakage Reverse	ALL	—	—	-100	nA	V_{GS} = -20V
I_{DSS} Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
		—	—	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$ On-State Drain Current ②	IRFJ220 IRFJ221	5.0	—	—	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
	IRFJ222 IRFJ223	4.0	—	—	A	
$R_{DS(on)}$ Static Drain-Source On-State Resistance ②	IRFJ220 IRFJ221	—	0.5	0.8	Ω	V_{GS} = 10V, I_D = 2.5A
	IRFJ222 IRFJ223	—	0.8	1.2	Ω	
g_{fs} Forward Transconductance ②	ALL	1.3	2.5	—	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 2.5A
C_{iss} Input Capacitance	ALL	—	450	600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss} Output Capacitance	ALL	—	150	300	pF	
C_{rss} Reverse Transfer Capacitance	ALL	—	40	80	pF	
$t_{d(on)}$ Turn-On Delay Time	ALL	—	20	40	ns	V_{DD} ≈ 0.5BV_{DSS}, I_D = 2.5A, Z_o = 50Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r Rise Time	ALL	—	30	60	ns	
$t_{d(off)}$ Turn-Off Delay Time	ALL	—	50	100	ns	
t_f Fall Time	ALL	—	30	60	ns	
Q_g Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	11	15	nC	V_{GS} = 10V, I_D = 6.0A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs} Gate-Source Charge	ALL	—	5.0	—	nC	
Q_{gd} Gate-Drain ("Miller") Charge	ALL	—	6.0	—	nC	
L_D Internal Drain Inductance	ALL	—	5.0	—	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die. — Modified MOSFET symbol showing the internal device inductances.
L_S Internal Source Inductance	ALL	—	12.5	—	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad. 

Thermal Resistance

R_{thJC} Junction-to-Case	ALL	—	—	3.1	K/W	
R_{thCS} Case-to-Sink	ALL	—	0.2	—	K/W	Mounting surface flat, smooth, and greased.
R_{thJA} Junction-to-Ambient	ALL	—	—	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ220 IRFJ221	—	—	5.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFJ222 IRFJ223	—	—	4.0	A	
I_{SM}	Pulse Source Current (Body Diode)③	IRFJ220 IRFJ221	—	—	20	A	
		IRFJ222 IRFJ223	—	—	16	A	
V_{SD}	Diode Forward Voltage ②	IRFJ220 IRFJ221	—	—	2.0	V	$T_C = 25°C, I_S = 5.0A, V_{GS} = 0V$
		IRFJ222 IRFJ223	—	—	1.8	V	$T_C = 25°C, I_S = 4.0A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	ALL	—	350	—	ns	$T_J = 150°C, I_F = 5.0A, dI_F/dt = 100A/\mu s$
Q_{RR}	Reverse Recovered Charge	ALL	—	2.3	—	μC	$T_J = 150°C, I_F = 5.0A, dI_F/dt = 100A/\mu s$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

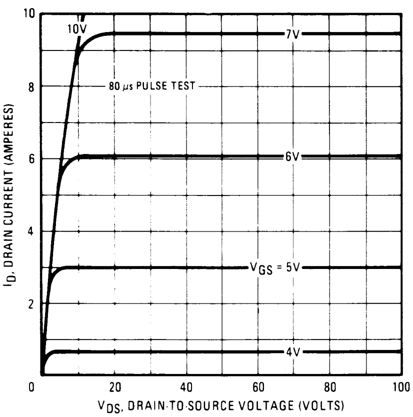


Fig. 1 — Typical Output Characteristics

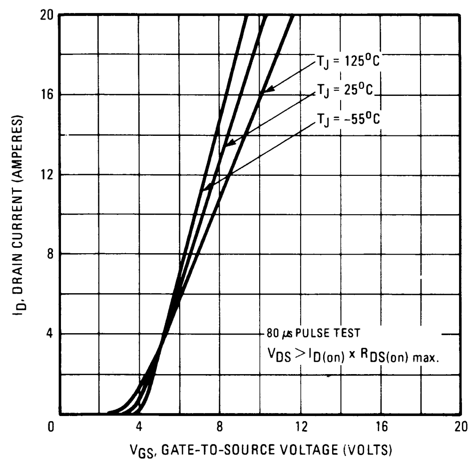


Fig. 2 — Typical Transfer Characteristics

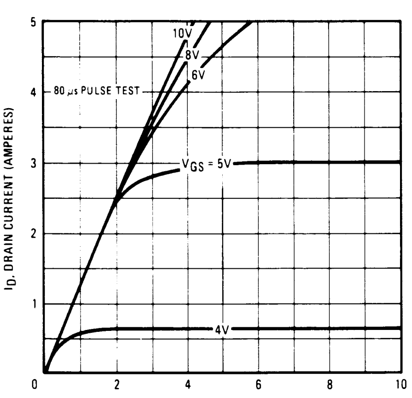


Fig. 3 — Typical Saturation Characteristics

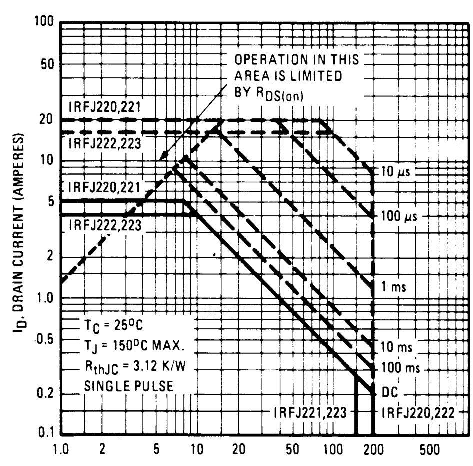


Fig. 4 — Maximum Safe Operating Area

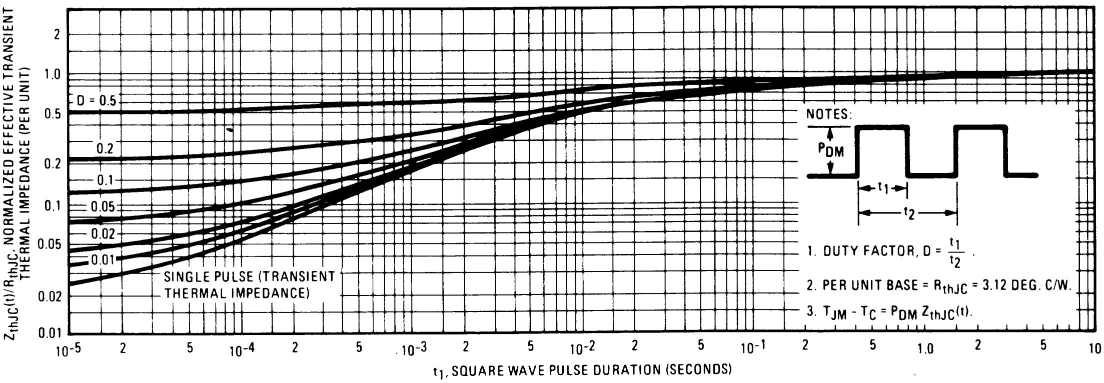


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

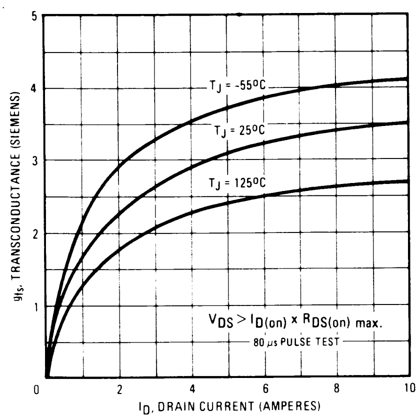


Fig. 6 — Typical Transconductance Vs. Drain Current

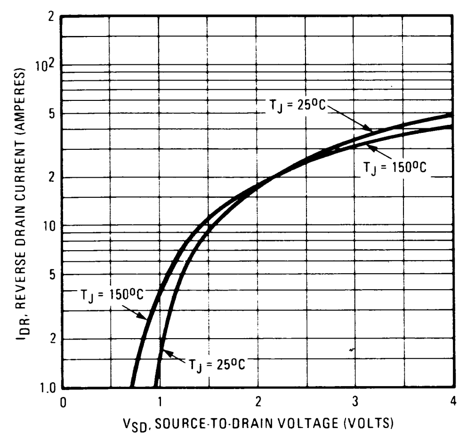


Fig. 7 — Typical Source-Drain Diode Forward Voltage

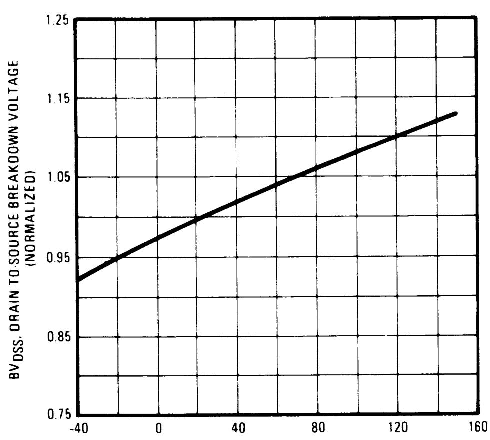


Fig. 8 — Breakdown Voltage Vs. Temperature

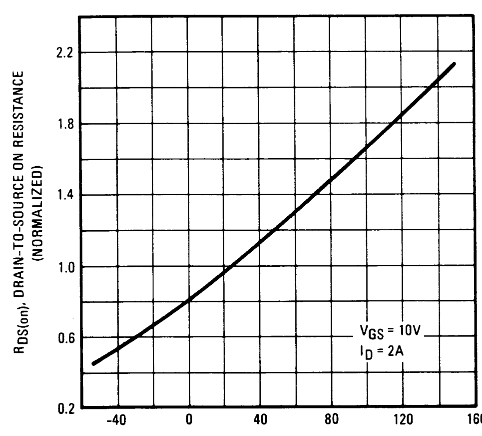


Fig. 9 — Normalized On-Resistance Vs. Temperature

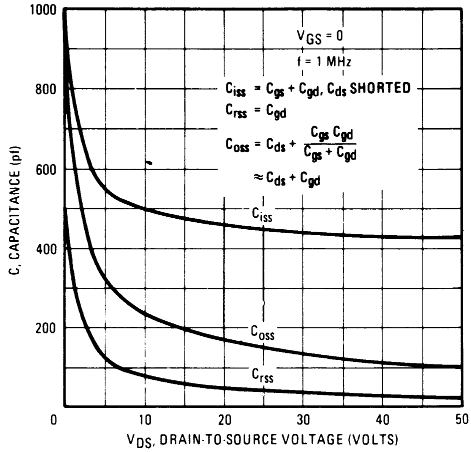


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

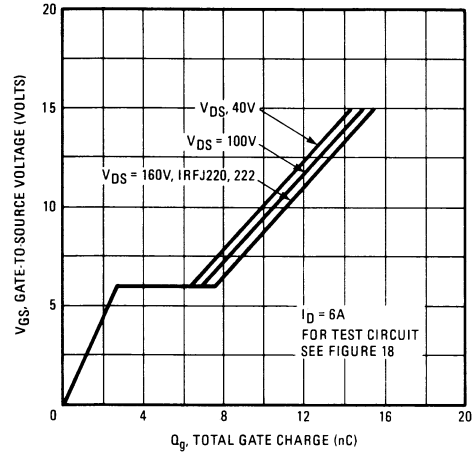


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

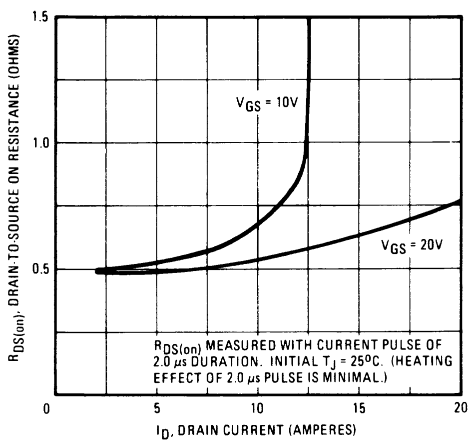


Fig. 12 — Typical On-Resistance Vs. Drain Current

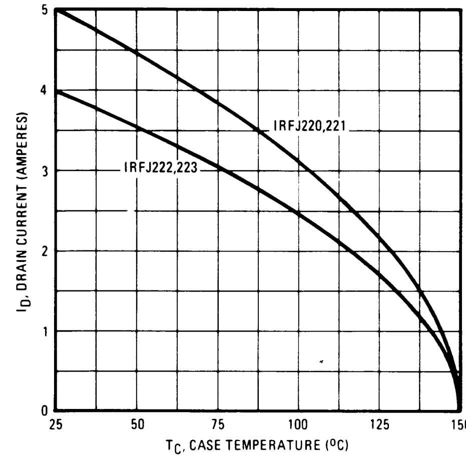


Fig. 13 — Maximum Drain Current Vs. Case Temperature

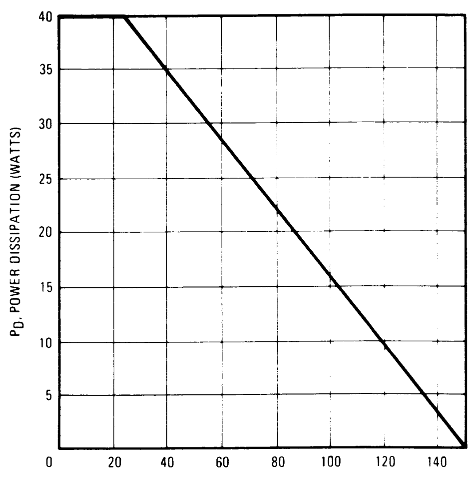


Fig. 14 — Power Vs. Temperature Derating Curve

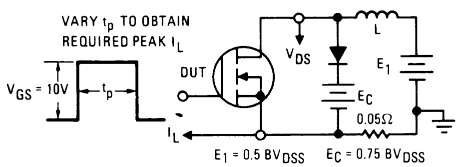


Fig. 15 — Clamped Inductive Test Circuit

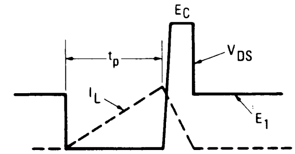


Fig. 16 — Clamped Inductive Waveforms

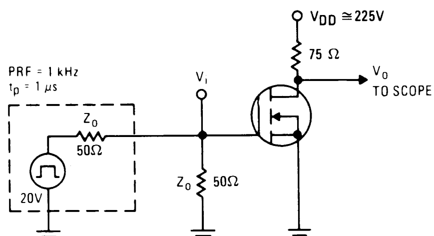


Fig. 17 — Switching Time Test Circuit

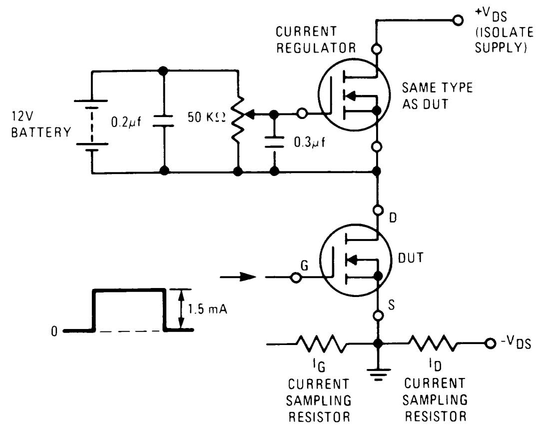


Fig. 18 — Gate Charge Test Circuit

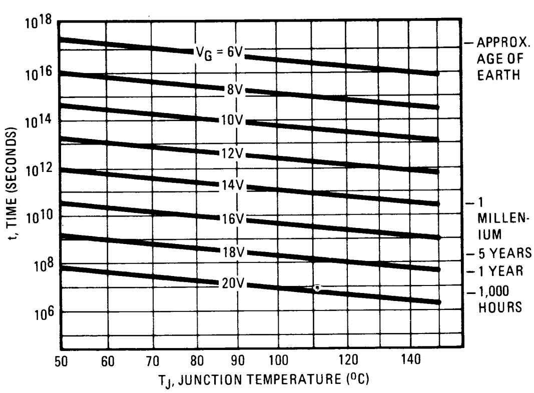


***Fig. 19 — Typical Time to Accumulated 1% Failure**

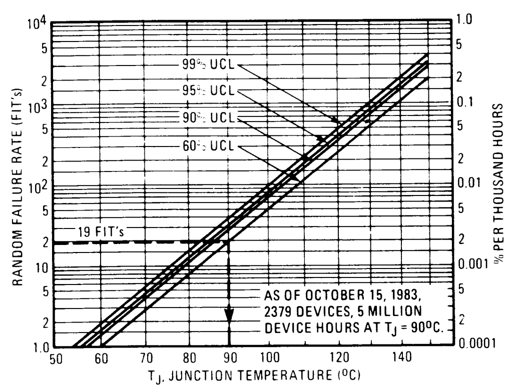


Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

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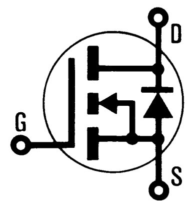

IRFJ230 IRFJ231 IRFJ232 IRFJ233

200 Volt, 0.4 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

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They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

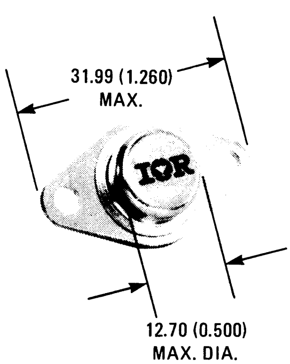
Features:

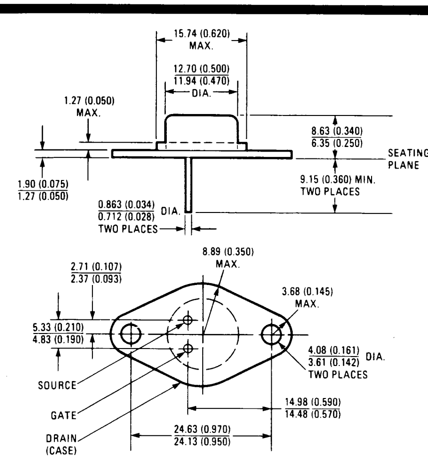
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ230	200V	0.4Ω	8.0A
IRFJ231	150V	0.4Ω	8.0A
IRFJ232	200V	0.6Ω	6.5A
IRFJ233	150V	0.6Ω	6.5A

CASE STYLE AND DIMENSIONS





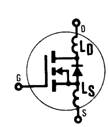
Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

IRFJ230, IRFJ231, IRFJ232, IRFJ233 Devices

Absolute Maximum Ratings

Parameter		IRFJ230	IRFJ231	IRFJ232	IRFJ233	Units
V_{DS}	Drain - Source Voltage ①	200	150	200	150	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	200	150	200	150	V
I_D @ T_C = 25°C	Continuous Drain Current	8.0	8.0	6.5	6.5	A
I_D @ T_C = 100°C	Continuous Drain Current	5.0	5.0	4.0	4.0	A
I_{DM}	Pulsed Drain Current ③	32	32	26	26	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	50 (See Fig. 14)				W
	Linear Derating Factor	0.4 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 32	32	26	26	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

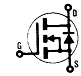
Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ230 IRFJ232	200	–	–	V	V_{GS} = 0V
		IRFJ231 IRFJ233	150	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ230 IRFJ231	8.0	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ232 IRFJ233	6.5	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ230 IRFJ231	–	0.25	0.4	Ω	V_{GS} = 10V, I_D = 4.0A
		IRFJ232 IRFJ233	–	0.4	0.6	Ω	
g_{fs}	Forward Transconductance ②	ALL	3.0	4.8	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 4.0A
C_{iss}	Input Capacitance	ALL	–	600	800	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	250	450	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	80	150	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	–	30	ns	V_{DD} = 90V, I_D = 4.0A, Z_o = 15Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	–	50	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	–	50	ns	
t_f	Fall Time	ALL	–	–	40	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	19	30	nC	V_{GS} = 10V, I_D = 10A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	10	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	9.0	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die. Modified MOSFET symbol showing the internal device inductances. 
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	2.5	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ230 IRFJ231	–	–	8.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFJ232 IRFJ233	–	–	6.5	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ230 IRFJ231	–	–	32	A	
		IRFJ232 IRFJ233	–	–	26	A	
V_{SD}	Diode Forward Voltage ②	IRFJ230 IRFJ231	–	–	2.0	V	$T_C = 25°C, I_S = 8.0A, V_{GS} = 0V$
		IRFJ232 IRFJ233	–	–	1.8	V	$T_C = 25°C, I_S = 6.5A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	ALL	–	450	–	ns	$T_J = 150°C, I_F = 8.0A, dI_F/dt = 100A/\mu s$
Q_{RR}	Reverse Recovered Charge	ALL	–	3.0	–	μC	$T_J = 150°C, I_F = 8.0A, dI_F/dt = 100A/\mu s$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① T_J = 25°C to 150°C. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

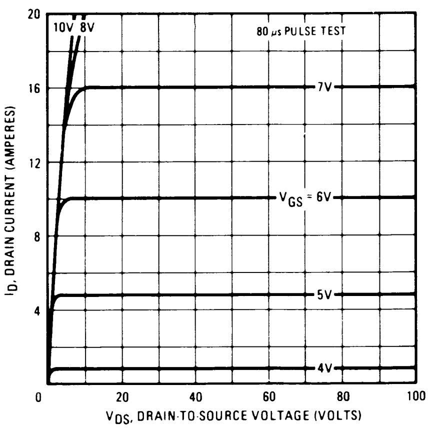


Fig. 1 – Typical Output Characteristics

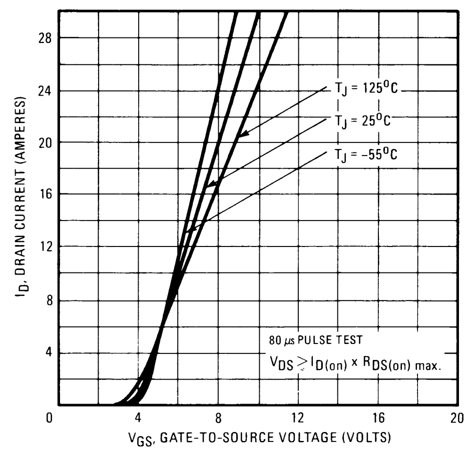


Fig. 2 – Typical Transfer Characteristics

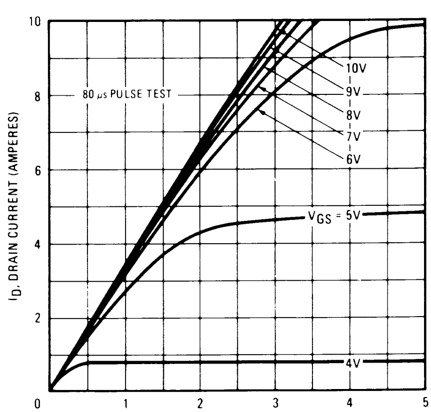


Fig. 3 – Typical Saturation Characteristics

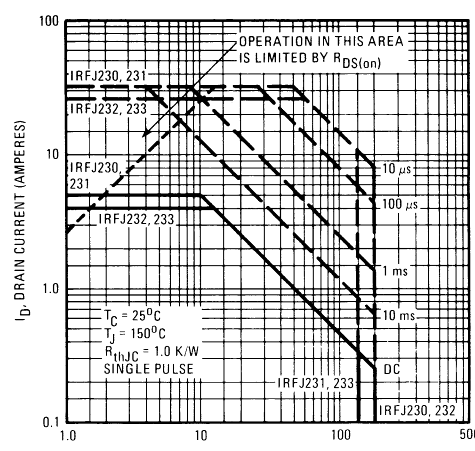


Fig. 4 – Maximum Safe Operating Area

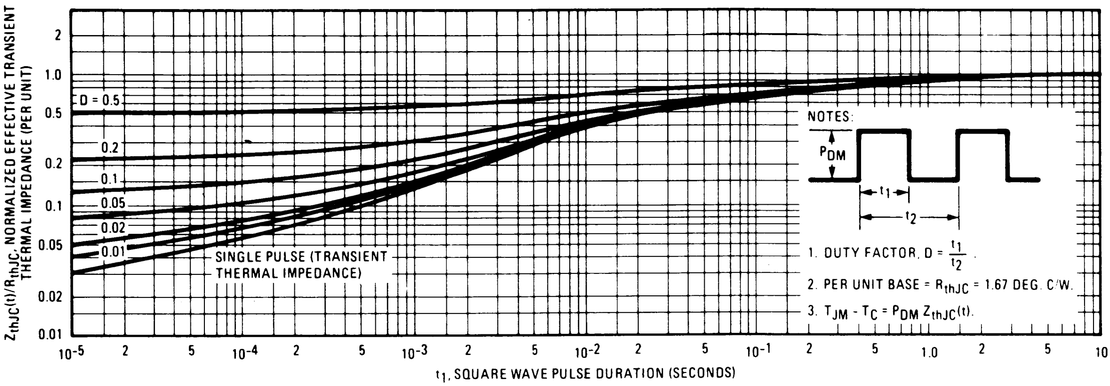


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

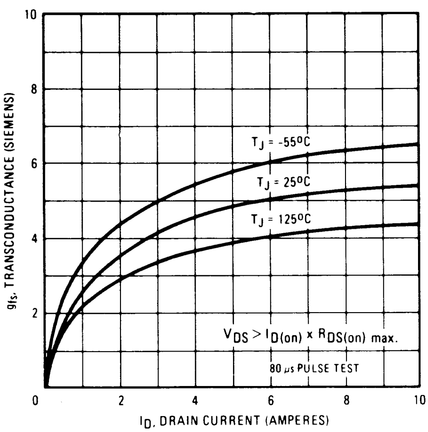


Fig. 6 — Typical Transconductance Vs. Drain Current

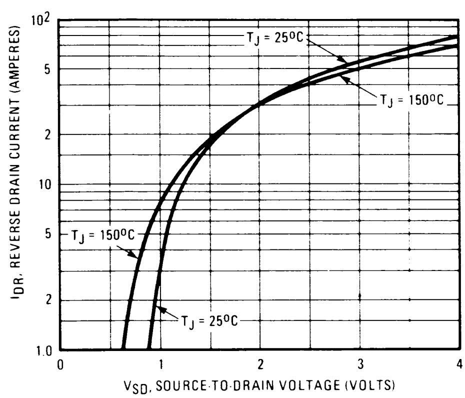


Fig. 7 — Typical Source-Drain Diode Forward Voltage

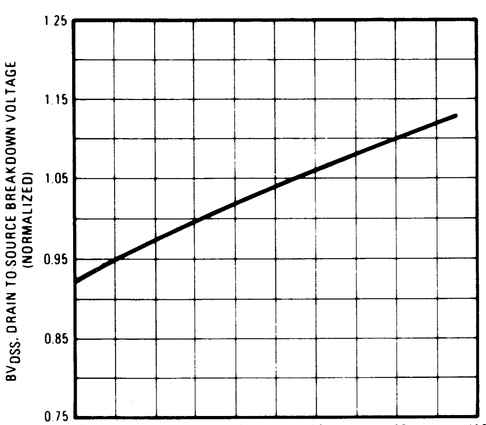


Fig. 8 — Breakdown Voltage Vs. Temperature

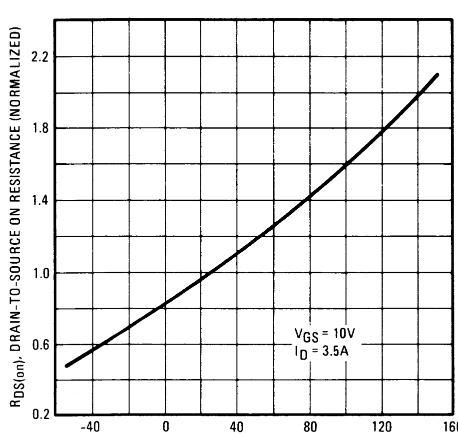


Fig. 9 — Normalized On-Resistance Vs. Temperature

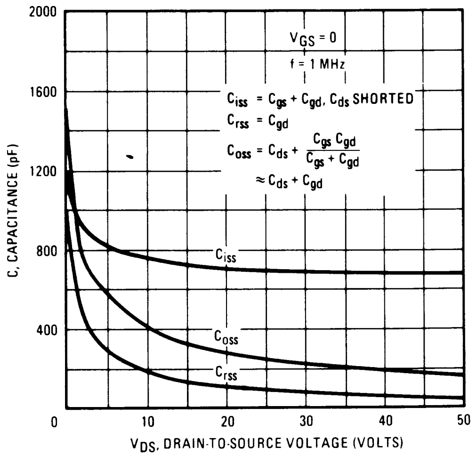


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

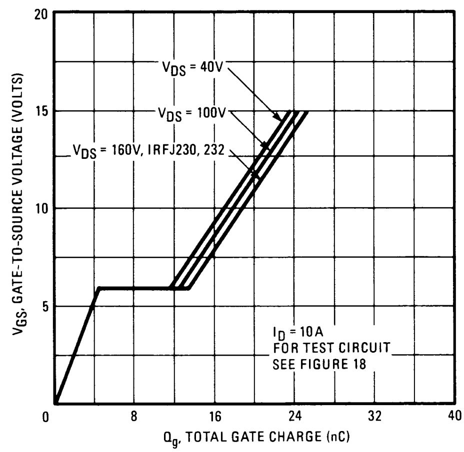


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

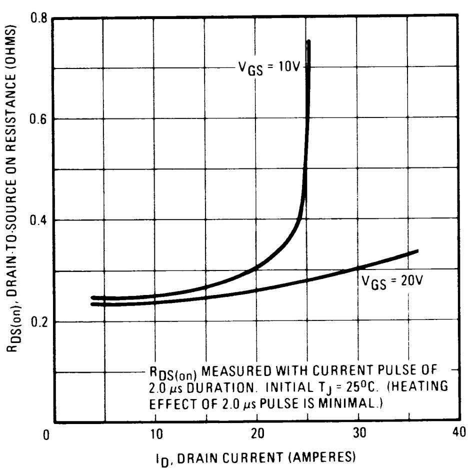


Fig. 12 — Typical On-Resistance Vs. Drain Current

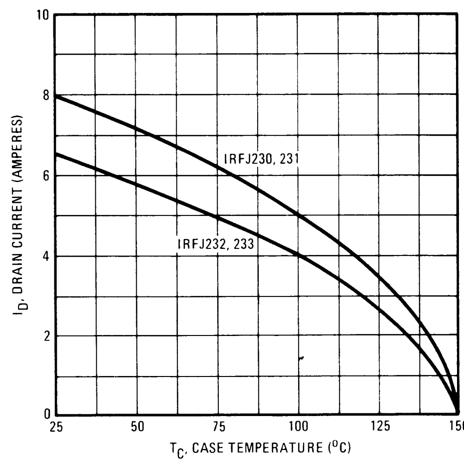


Fig. 13 — Maximum Drain Current Vs. Case Temperature

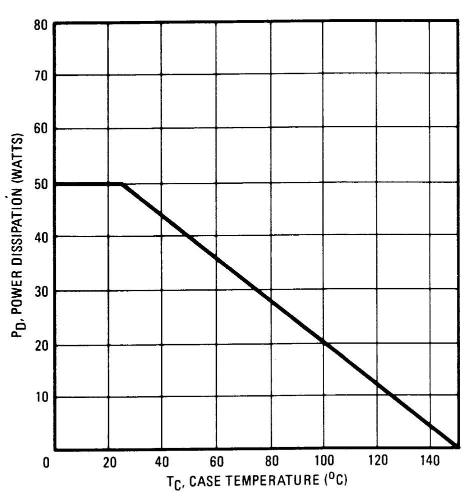


Fig. 14 — Power Vs. Temperature Derating Curve

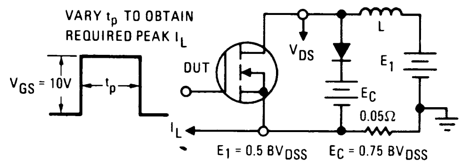


Fig. 15 — Clamped Inductive Test Circuit

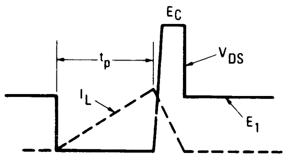


Fig. 16 — Clamped Inductive Waveforms

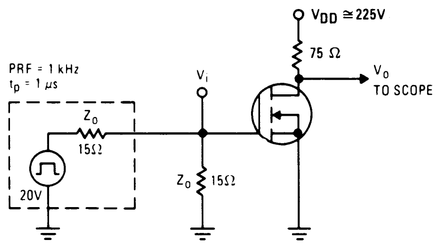


Fig. 17 — Switching Time Test Circuit

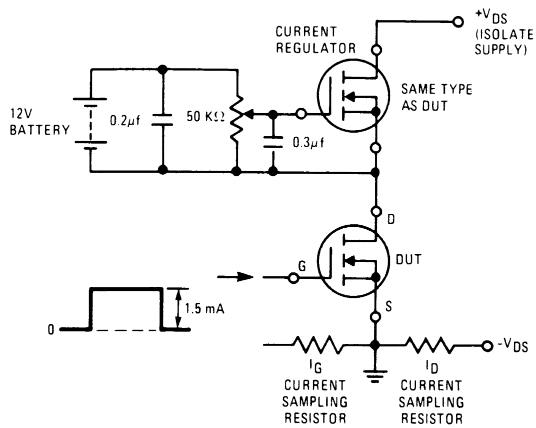


Fig. 18 — Gate Charge Test Circuit

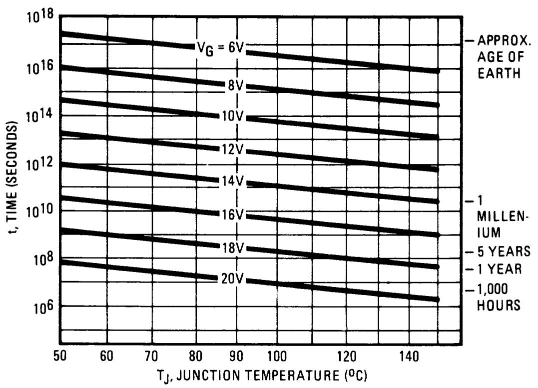


***Fig. 19 — Typical Time to Accumulated 1% Failure**

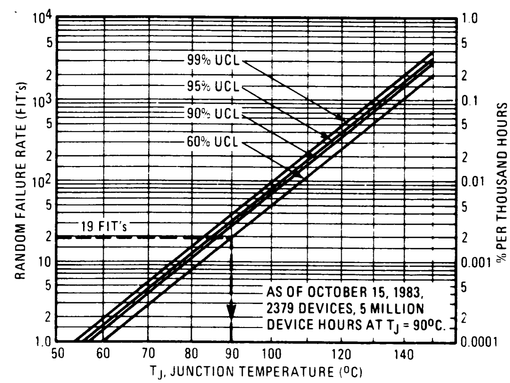


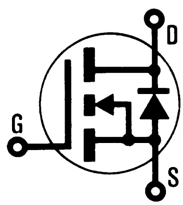
Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

* The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRFJ240 IRFJ241 IRFJ242 IRFJ243

N-CHANNEL POWER MOSFETs



200 Volt, 0.2 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

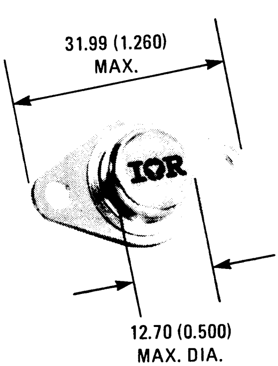
Features:

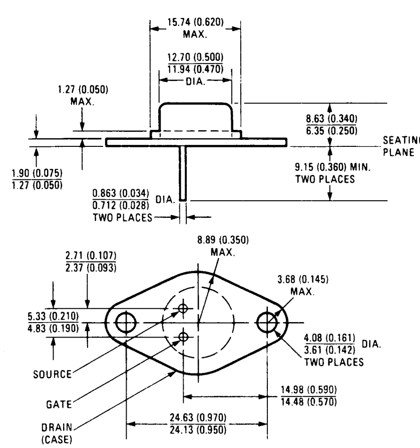
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ240	200V	0.18Ω	13A
IRFJ241	150V	0.18Ω	13A
IRFJ242	200V	0.22Ω	11A
IRFJ243	150V	0.22Ω	11A

CASE STYLE AND DIMENSIONS





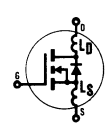
Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

IRFJ240, IRFJ241, IRFJ242, IRFJ243 Devices

Absolute Maximum Ratings

	Parameter	IRFJ240	IRFJ241	IRFJ242	IRFJ243	Units
V_{DS}	Drain - Source Voltage ①	200	150	200	150	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 kΩ) ①	200	150	200	150	V
I_D @ T_C = 25°C	Continuous Drain Current	13	13	11	11	A
I_D @ T_C = 100°C	Continuous Drain Current	8.0	8.0	7.0	7.0	A
I_{DM}	Pulsed Drain Current ③	50	50	40	40	A
V_{GS}	Gate - Source Voltage	± 20				V
P_D @ T_C = 25°C	Max. Power Dissipation	70 (See Fig. 14)				W
	Linear Derating Factor	0.56 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 50	50	40	40	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	−55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for10s)				°C

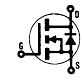
Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

	Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ240 IRFJ242	200	–	–	V	V_{GS} = 0V
		IRFJ241 IRFJ243	150	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	−100	nA	V_{GS} = −20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ240 IRFJ241	13	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ242 IRFJ243	11	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ240 IRFJ241	–	0.14	0.18	Ω	V_{GS} = 10V, I_D = 7.0A
		IRFJ242 IRFJ243	–	0.20	0.22	Ω	
g_{fs}	Forward Transconductance ②	ALL	6.0	9.0	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 7.0A
C_{iss}	Input Capacitance	ALL	–	1275	1600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	500	750	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	160	300	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	16	30	ns	V_{DD} ≈ 75V, I_D = 7.0A, Z_o = 4.7Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	27	60	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	40	80	ns	
t_f	Fall Time	ALL	–	31	60	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	43	60	nC	V_{GS} = 10V, I_D = 16A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	16	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	27	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die. / Modified MOSFET symbol showing the internal device inductances.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad. 

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	1.8	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ240 IRFJ241	–	–	13	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFJ242 IRFJ243	–	–	11	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ240 IRFJ241	–	–	50	A	
		IRFJ242 IRFJ243	–	–	40	A	
V_{SD}	Diode Forward Voltage ②	IRFJ240 IRFJ241	–	–	2.0	V	$T_C = 25°C, I_S = 13A, V_{GS} = 0V$
		IRFJ242 IRFJ243	–	–	1.9	V	$T_C = 25°C, I_S = 11A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	ALL	–	650	–	ns	$T_J = 150°C, I_F = 13A, dI_F/dt = 100A/\mu s$
Q_{RR}	Reverse Recovered Charge	ALL	–	4.1	–	μC	$T_J = 150°C, I_F = 13A, dI_F/dt = 100A/\mu s$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①$T_J = 25°C$ to $150°C$. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

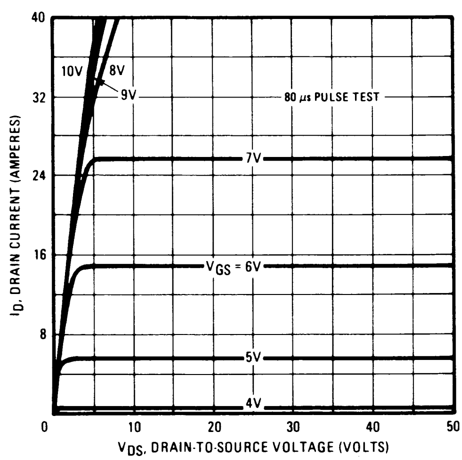


Fig. 1 — Typical Output Characteristics

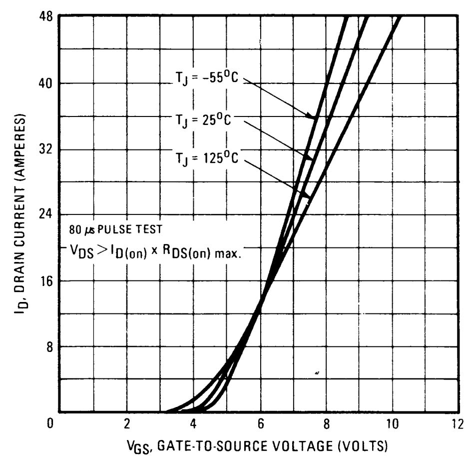


Fig. 2 — Typical Transfer Characteristics

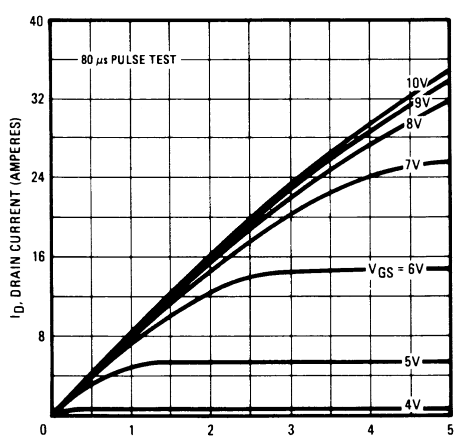


Fig. 3 — Typical Saturation Characteristics

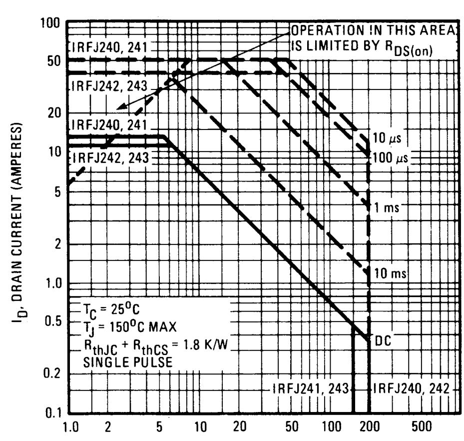


Fig. 4 — Maximum Safe Operating Area

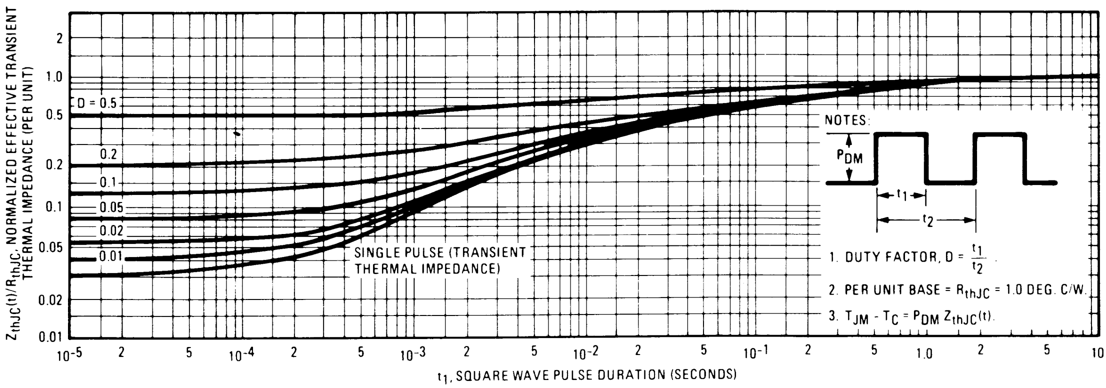


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

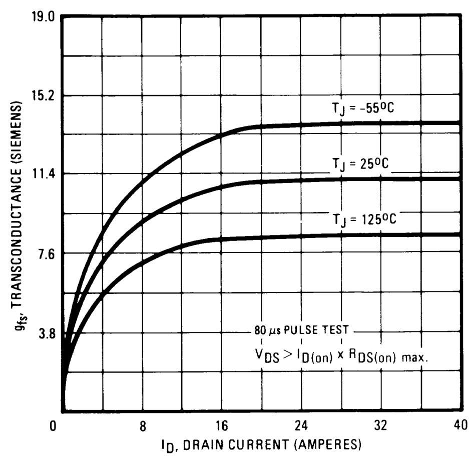


Fig. 6 — Typical Transconductance Vs. Drain Current

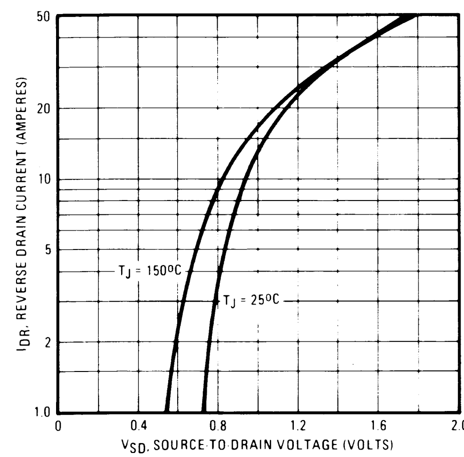


Fig. 7 — Typical Source-Drain Diode Forward Voltage

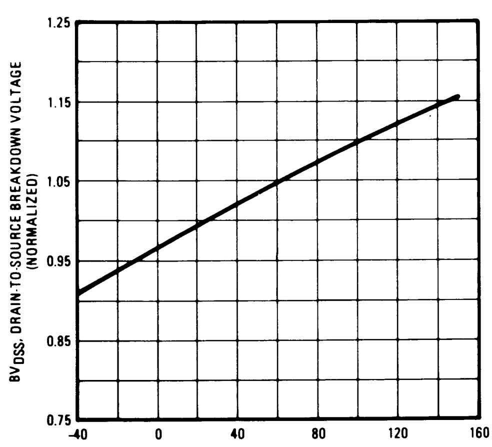


Fig. 8 — Breakdown Voltage Vs. Temperature

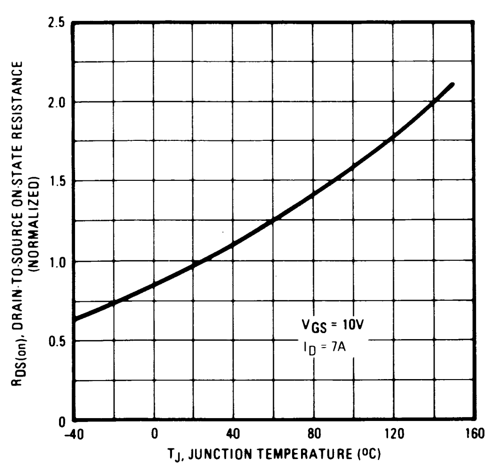


Fig. 9 — Normalized On-Resistance Vs. Temperature

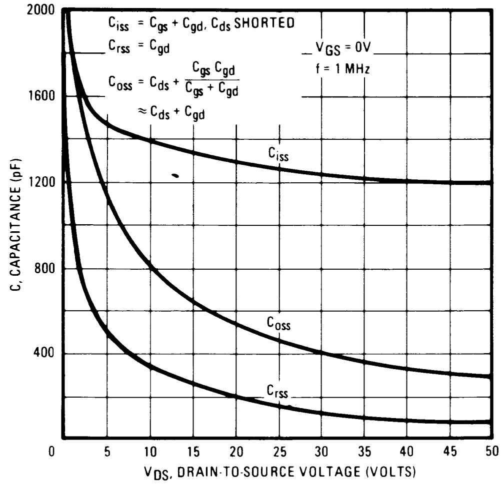


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

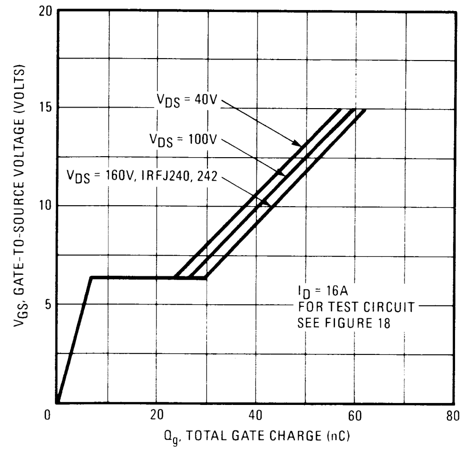


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

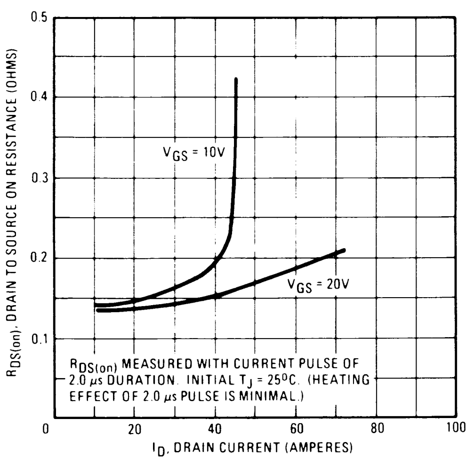


Fig. 12 — Typical On-Resistance Vs. Drain Current

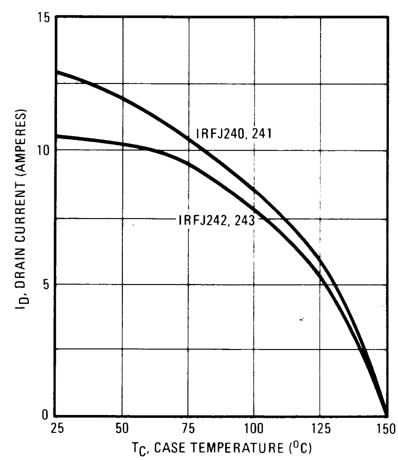


Fig. 13 — Maximum Drain Current Vs. Case Temperature

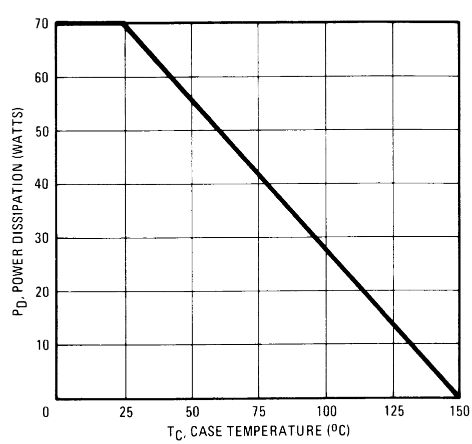


Fig. 14 — Power Vs. Temperature Derating Curve

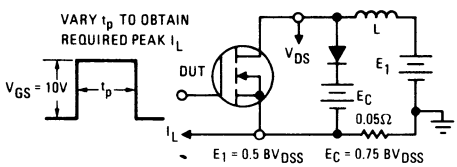


Fig. 15 – Clamped Inductive Test Circuit

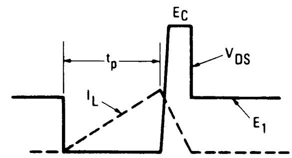


Fig. 16 – Clamped Inductive Waveforms

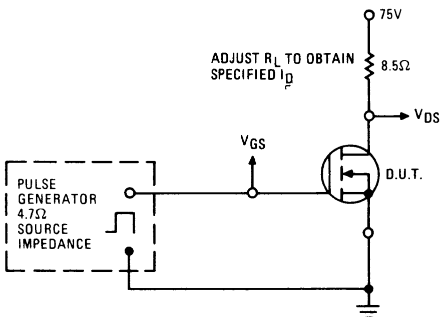


Fig. 17 – Switching Time Test Circuit

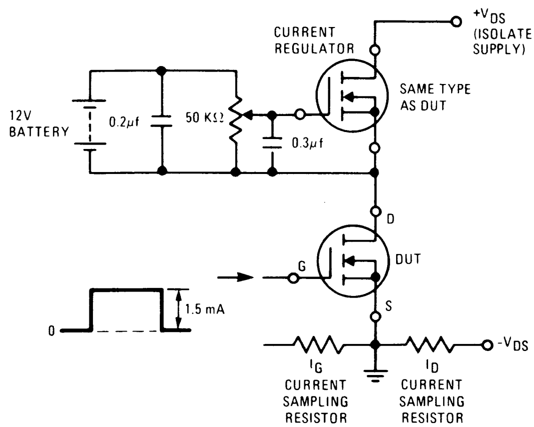
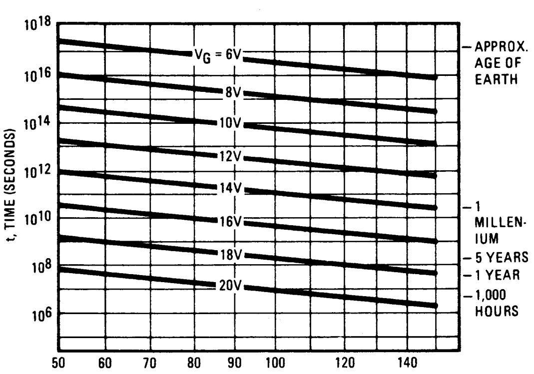


Fig. 18 – Gate Charge Test Circuit



*** Fig. 19 – Typical Time to Accumulated 1% Failure**

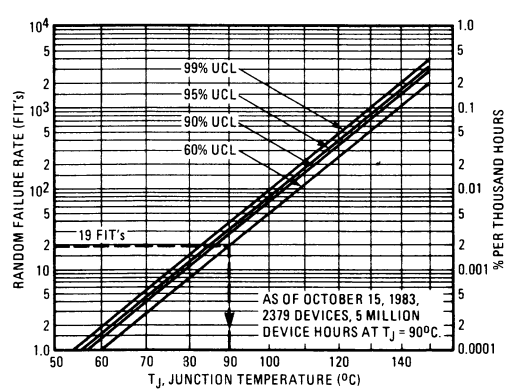


Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.